Abstract Submitted
for the MAR13 Meeting of
The American Physical Society

Oxygen vacancy formation in doped ceria: Effects of electron localization and ion local distortion$^1$ ZHENPENG HU, Nankai University — Density functional theory with plus U approximation has been used to study property of doped ceria, especially oxygen vacancy formation energy on doped CeO$_2$ surface. Surfaces with substitutional dopants having lower valence than Ce(IV) have been studied in detail. Based on our results, there are two factors affecting the formation energy of oxygen vacancy: electron localization to form polaron, and local distortion around dopant while vacancy generating. We discuss related application for these rules in catalysis process.

$^1$Fundamental Research Funds for the Central Universities (65012331)